

N-channel 100 V, 4.9 mΩ typ., 110 A, STripFET™ F7
Power MOSFETs in H²PAK-2 and H²PAK-6 packages

Datasheet - production data

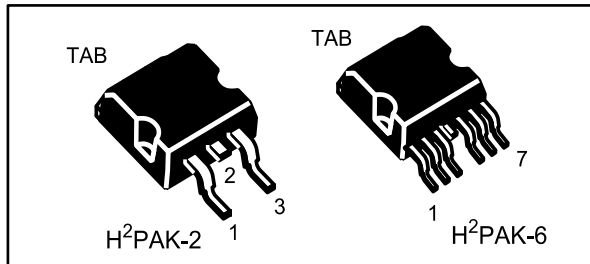
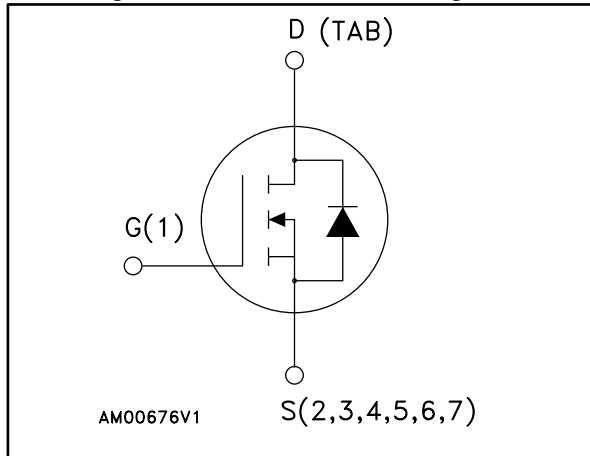


Figure 1: Internal schematic diagram



Features

Order codes	V _{DS}	R _{DS(on)} max.	I _D	P _{TOT}
STH110N10F7-2	100 V	6.5 mΩ	110 A	150 W
STH110N10F7-6				

- Among the lowest R_{DS(on)} on the market
- Excellent figure of merit (FoM)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

These N-channel Power MOSFETs utilize STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Table 1: Device summary

Order codes	Marking	Package	Packing
STH110N10F7-2	110N10F7	H ² PAK-2	Tape and reel
STH110N10F7-6		H ² PAK-6	

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	110	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	76	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^{\circ}\text{C}$	18	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^{\circ}\text{C}$	13	A
$I_{DM}^{(3)}$	Drain current (pulsed)	430	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	150	W
$E_{AS}^{(4)}$	Single pulse avalanche energy	490	mJ
T_J	Operating junction temperature	-55 to 175	$^{\circ}\text{C}$
T_{stg}	Storage temperature		$^{\circ}\text{C}$

Notes:

⁽¹⁾This value is rated according to R_{thj-c}

⁽²⁾This value is rated according to $R_{thj-pcb}$

⁽³⁾Pulse width limited by safe operating area

⁽⁴⁾Starting $T_J = 25\text{ }^{\circ}\text{C}$, $I_D = 18$, $V_{DD} = 50\text{ V}$

Table 3: Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1	$^{\circ}\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	35	$^{\circ}\text{C/W}$

Notes:

⁽¹⁾When mounted on FR-4 board of 1 inch², 2 oz Cu, $t < 10$ seconds

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4: On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage (V _{GS} = 0)	I _D = 250 μA	100			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = 100 V			1	μA
		V _{DS} = 100 V; T _C = 125 °C			10	μA
I _{GSS}	Gate body leakage current (V _{DS} = 0)	V _{GS} = 20 V			100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.5		4.5	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 55 A		4.9	6.5	μΩ

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 50 V, f = 1 MHz, V _{GS} = 0	-	5117	-	pF
C _{oss}	Output capacitance			992		pF
C _{rss}	Reverse transfer capacitance			39		pF
Q _g	Total gate charge	V _{DD} = 50 V, I _D = 110 A	-	72	-	nC
Q _{gs}	Gate-source charge	V _{GS} = 10 V		31		nC
Q _{gd}	Gate-drain charge	See Figure 14: "Gate charge test circuit"		16		nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 50 V, I _D = 55 A, R _G = 4.7 Ω, V _{GS} = 10 V See Figure 13: "Switching times test circuit for resistive load"	-	25	-	ns
t _r	Rise time			36		ns
t _{d(off)}	Turn-off delay time			52		ns
t _f	Fall time			21		ns

Table 7: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I _{SD}	Source-drain current		-		110	A
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)				430	A
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 55 A, V _{GS} = 0			1.2	V
t _{rr}	Reverse recovery time	I _{SD} = 110 A, di/dt = 100 A/μs, V _{DD} = 80 V, T _j = 150 °C		77		ns
Q _{rr}	Reverse recovery charge			150		nC
I _{RRM}	Reverse recovery current			4.3		A

Notes:

⁽¹⁾Pulse width limited by safe operating area

⁽²⁾Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

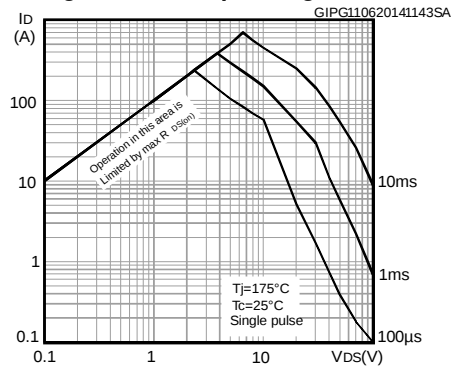


Figure 3: Thermal impedance

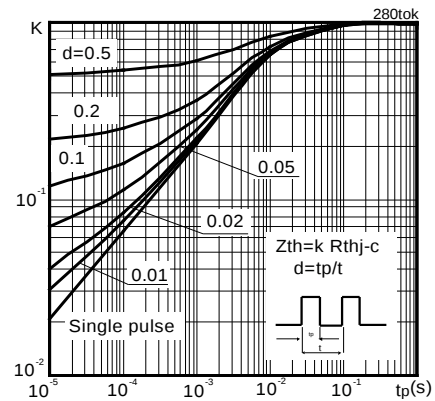


Figure 4: Output characteristics

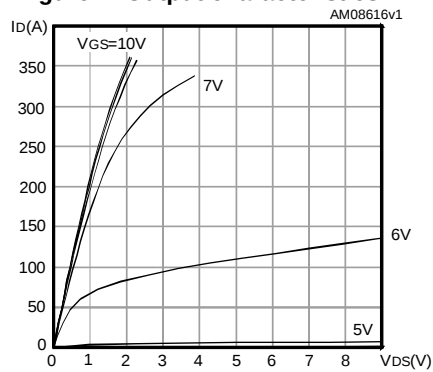


Figure 5: Transfer characteristics

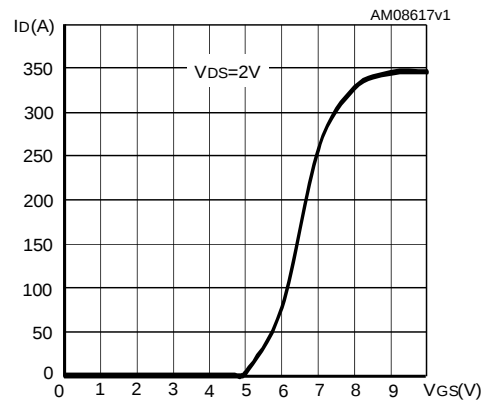
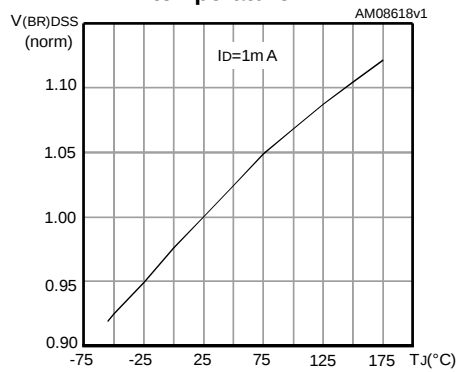
Figure 6: Normalized $V_{(BR)DSS}$ vs temperature

Figure 7: Static drain-source on-resistance

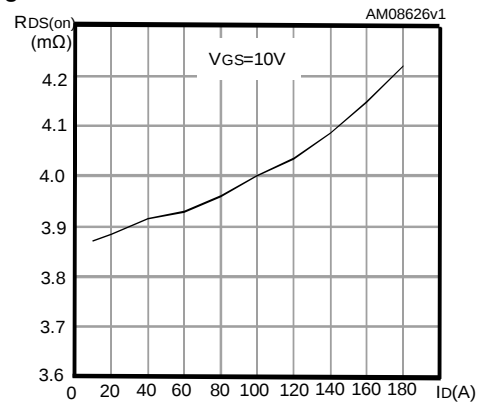


Figure 8: Gate charge vs gate-source voltage

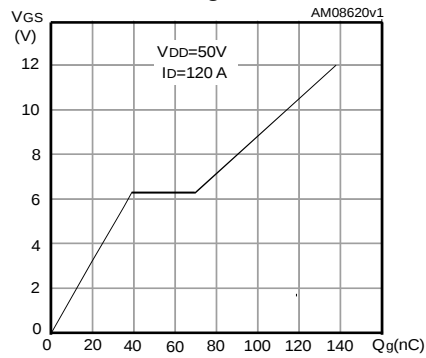


Figure 9: Capacitance variations

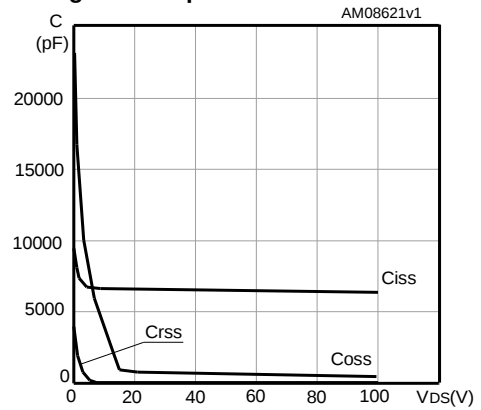


Figure 10: Normalized gate threshold voltage vs temperature

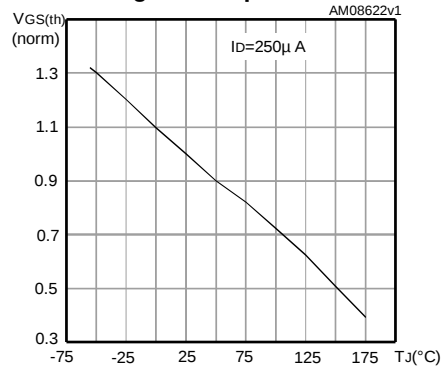


Figure 11: Normalized on-resistance vs temperature

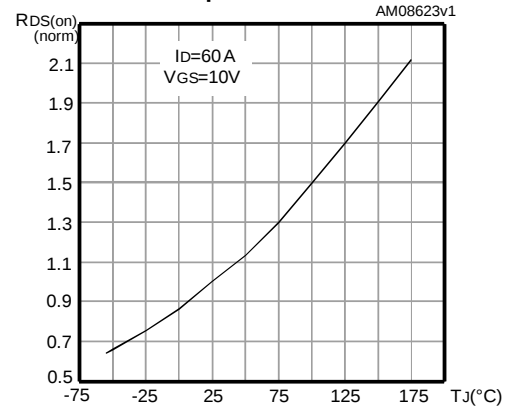
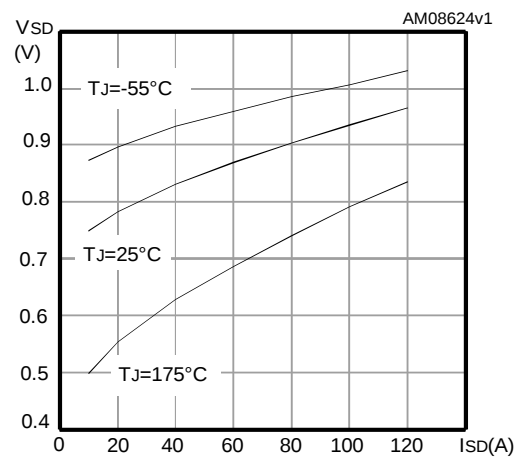
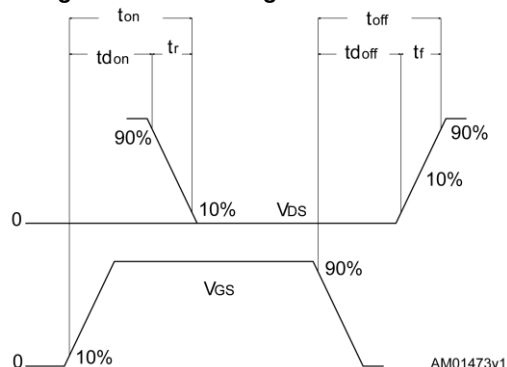


Figure 12: Source-drain diode forward characteristics





4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK[®] is an ST trademark.

4.1 H²PAK-2 package information

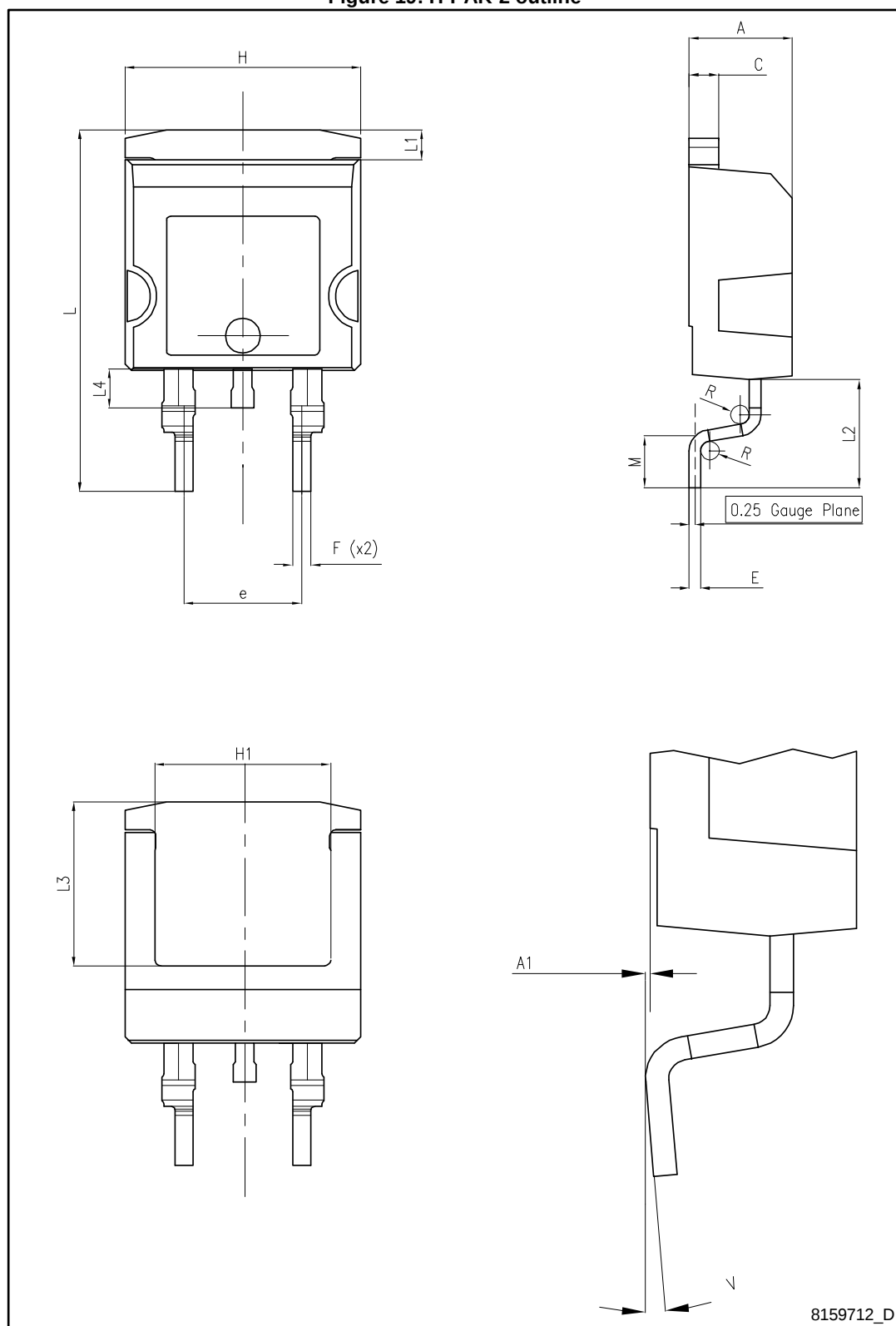
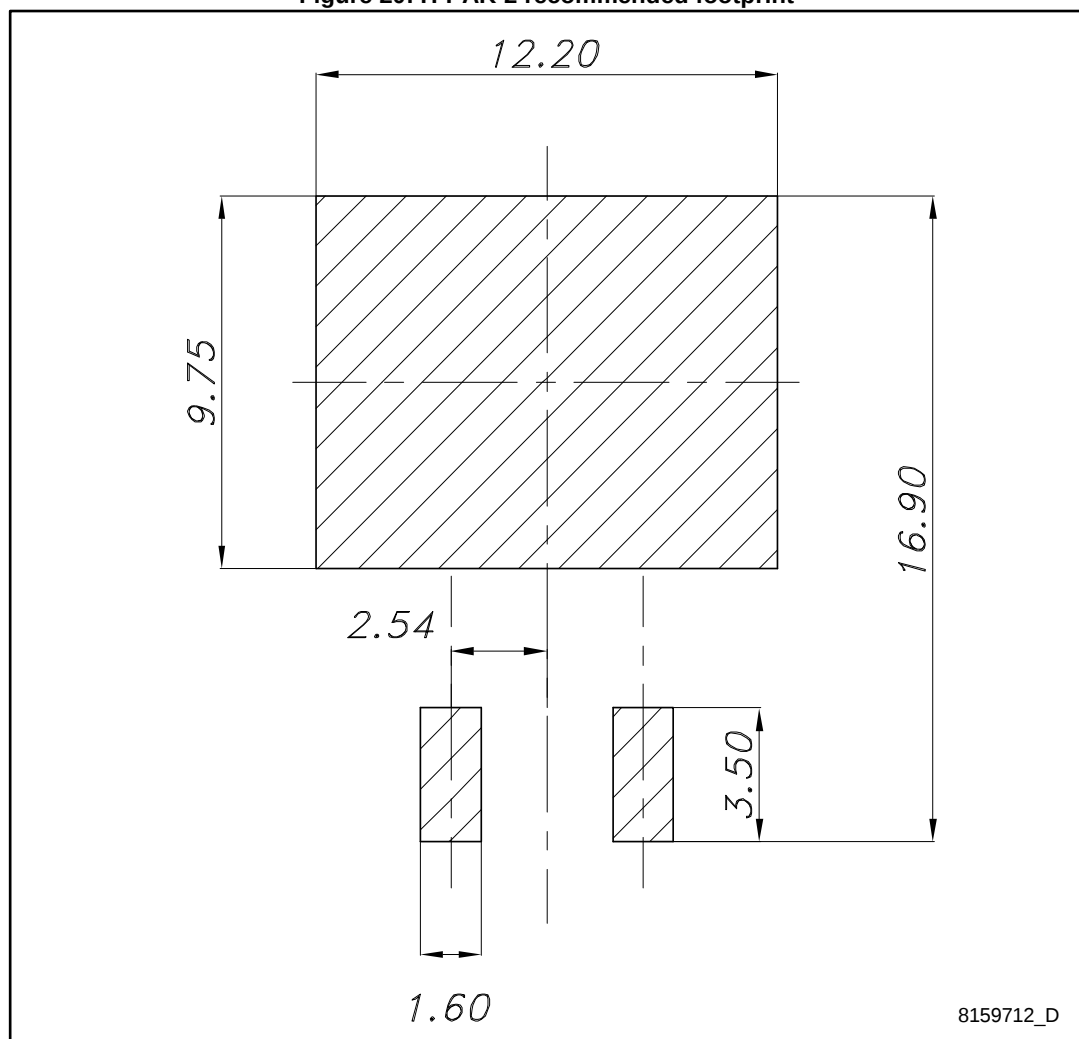
Figure 19: H²PAK-2 outline

Table 8: H²PAK-2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30	-	4.80
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

Figure 20: H²PAK-2 recommended footprint

4.2 H²PAK-6 package information

Figure 21: H²PAK-6 outline

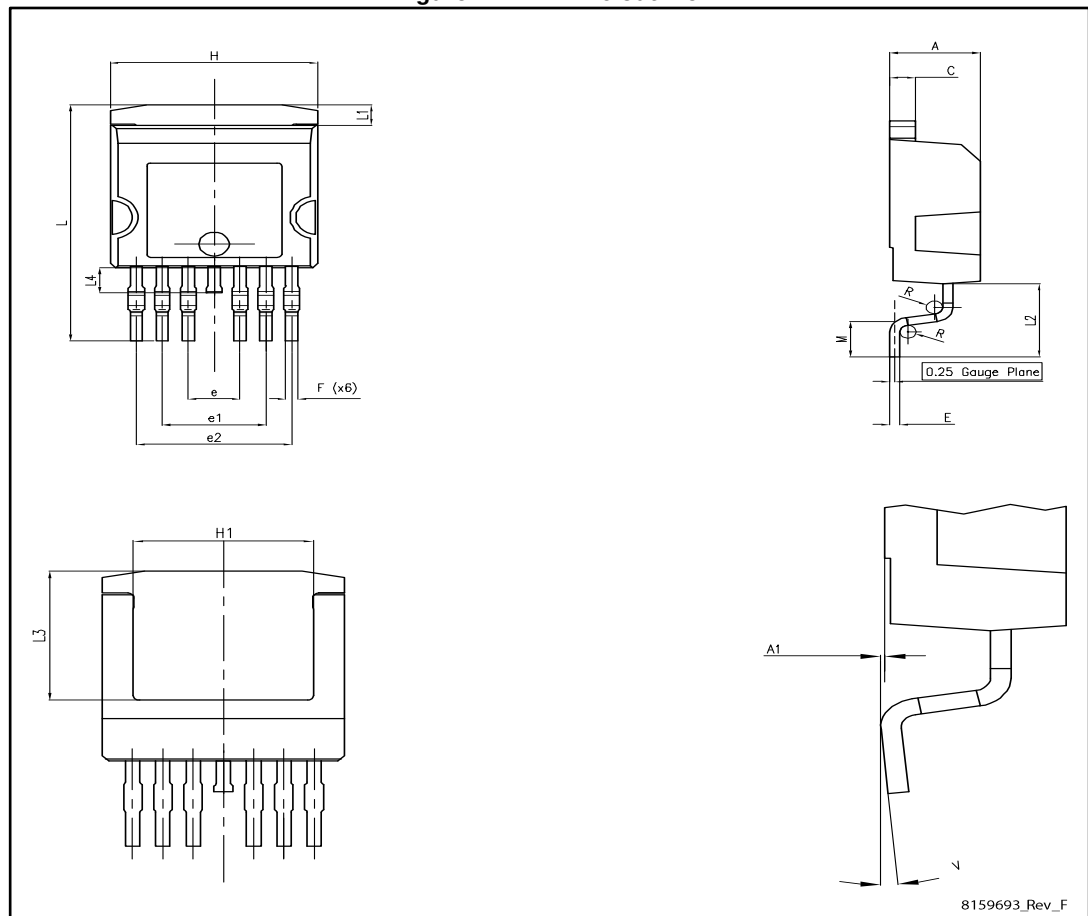
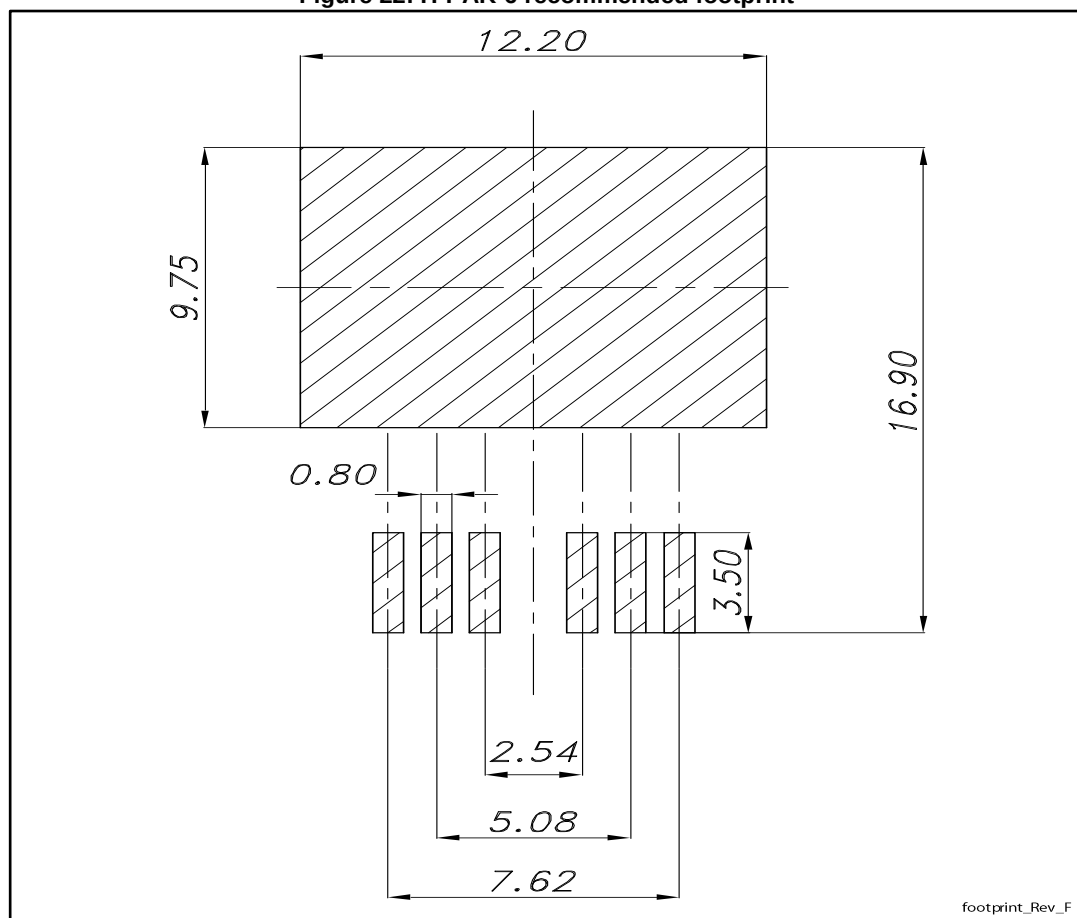


Table 9: H²PAK-6 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30	-	4.80
A1	0.03		0.20
C	1.17		1.37
e	2.34		2.74
e1	4.88		5.28
e2	7.42		7.82
E	0.45		0.60
F	0.50		0.70
H	10.00		10.40
H1	7.40		7.80
L	14.75		15.25
L1	1.27		1.40
L2	4.35		4.95
L3	6.85		7.25
L4	1.5		1.75
M	1.90		2.50
R	0.20		0.60
V	0°		8°

Figure 22: H²PAK-6 recommended footprint



Dimensions are in mm.

4.3

Figure 23: Tape outline

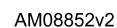


Figure 24: Reel outline

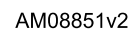


Table 10: Tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

5 Revision history

Table 11: Document revision history

Date	Revision	Changes
10-Dec-2012	1	Initial release. Part number (STH110N10F7-2) previously included in datasheet ID024005
16-Jul-2013	2	• Modified: title • Modified: I_{DM} value in Table 2: "Absolute maximum ratings", the entire typical values in Table 5: "Dynamic", Table 6: "Switching times" and Table 7: "Source-drain diode" • Modified: test circuit section • Minor text changes
11-Nov-2014	3	• Updated: H²PAK-6 package information. • Updated the title, features and description. • Minor text changes.

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